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BSS84

P-Channel Mosfet

www.sot23.com.tw

Product Summary

- V_{DS} -50V
- I_D -0.13A
- $R_{DS(ON)}$(at V_{GS}=-10V) ＜5 mohm
- $R_{DS(ON)}$(at V_{GS}=-4.5V) ＜6 mohm

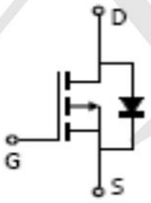
Application

- Battery protection
- Load switch
- Power management

Package and Pin Configuration

SOT-23

Circuit diagram



Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-50	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current	I_D	-0.13	A
Pulsed Drain Current (note 1) @tp <10 μs	I_{DM}	-0.52	A
Power Dissipation	P_D	225	mW
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	556	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃
Maximum Lead Temperature for Soldering Purposes , Duration for 5 Seconds	T_L	260	℃

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =-250μA	-50			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =-50V,V_{GS} = 0V			-15	μA
		V_{DS} =-25V,V_{GS} = 0V			-0.1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V			±5	μA
Gate threshold voltage (note 3)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =-250μA	-0.9	-1.6	-2	V
Drain-source on-resistance (note 3)	$R_{DS(on)}$	V_{GS} =-5V, I_D =-0.1A		4	5	Ω
		V_{GS} =-10V, I_D =-0.1A		4.5	6	Ω
Forward transconductance (note 1)	g_{FS}	V_{DS}=-25V; I_D=-100mA	50			mS
DYNAMIC CHARACTERISTICS (note 4)						
Input capacitance	C_{iss}	V_{DS} =5V,V_{GS} =0V,f =1MHz		30		pF
Output capacitance	C_{oss}			10		pF
Reverse transfer capacitance	C_{rss}			5		pF
SWITCHING CHARACTERISTICS (note 4)						
Turn-on delay time	$t_{d(on)}$	V_{DD}=-15V, R_L=50Ω, I_D =-2.5A		2.5		ns
Turn-on rise time	t_r			1		ns
Turn-off delay time	$t_{d(off)}$			16		ns
Turn-off fall time	t_f			8		ns
SOURCE−DRAIN DIODE CHARACTERISTICS						
Continuous Current	I_S				-0.13	A
Pulsed Current	I_{SM}				-0.52	A
Diode forward voltage (note 3)	V_{SD}	I_S=-0.13A, V_{GS} = 0V			-2.2	V

Typical Electrical and Thermal Characteristics

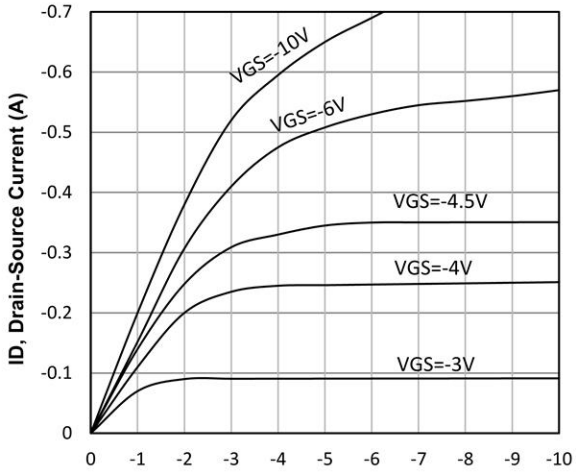


Fig1. Typical Output Characteristics

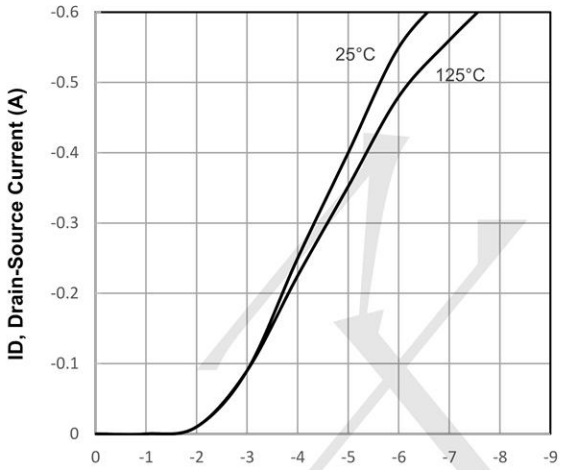


Fig2. Typical Transfer Cha racteristics

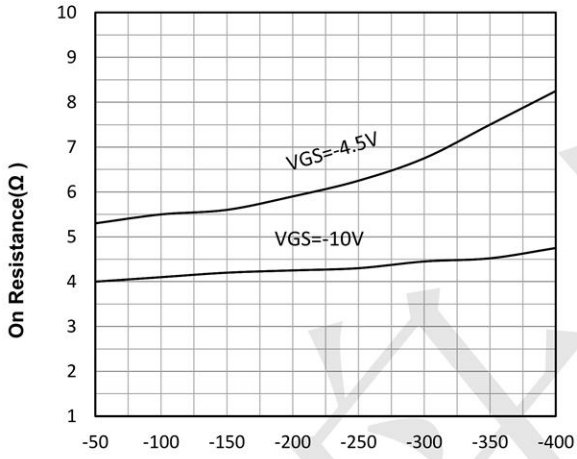


Fig3. Drain-Source on Resistance

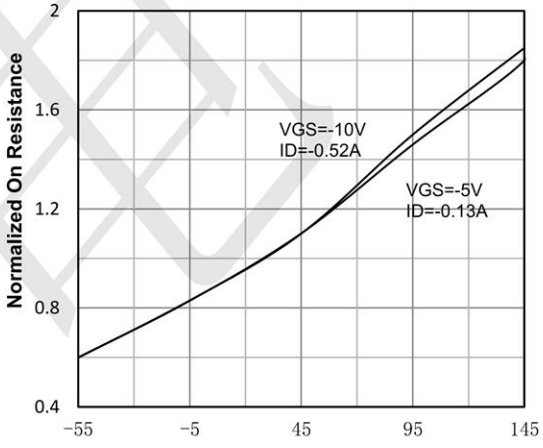


Fig4. Normalized On-Resistance Vs. Temperature

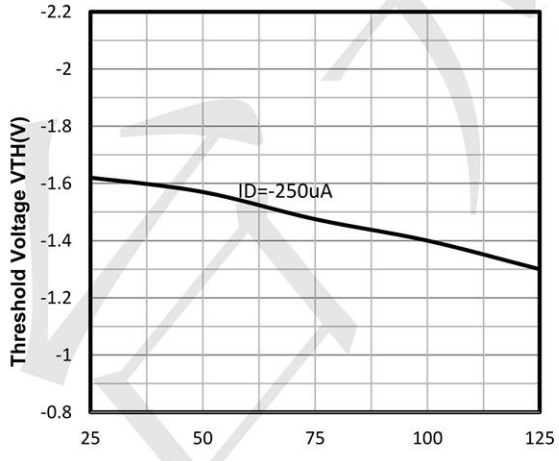


Fig5. Gate Threshold vs. Junction Temperature

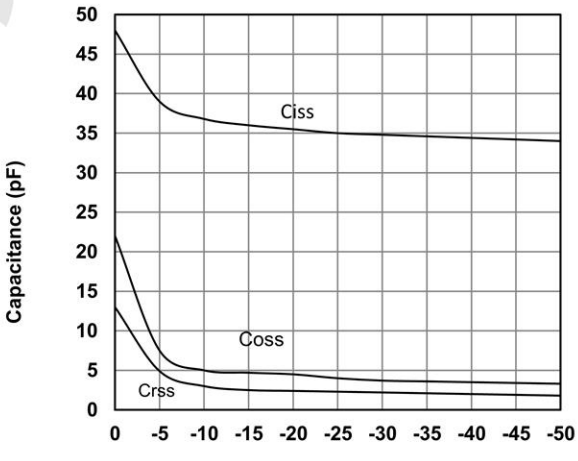
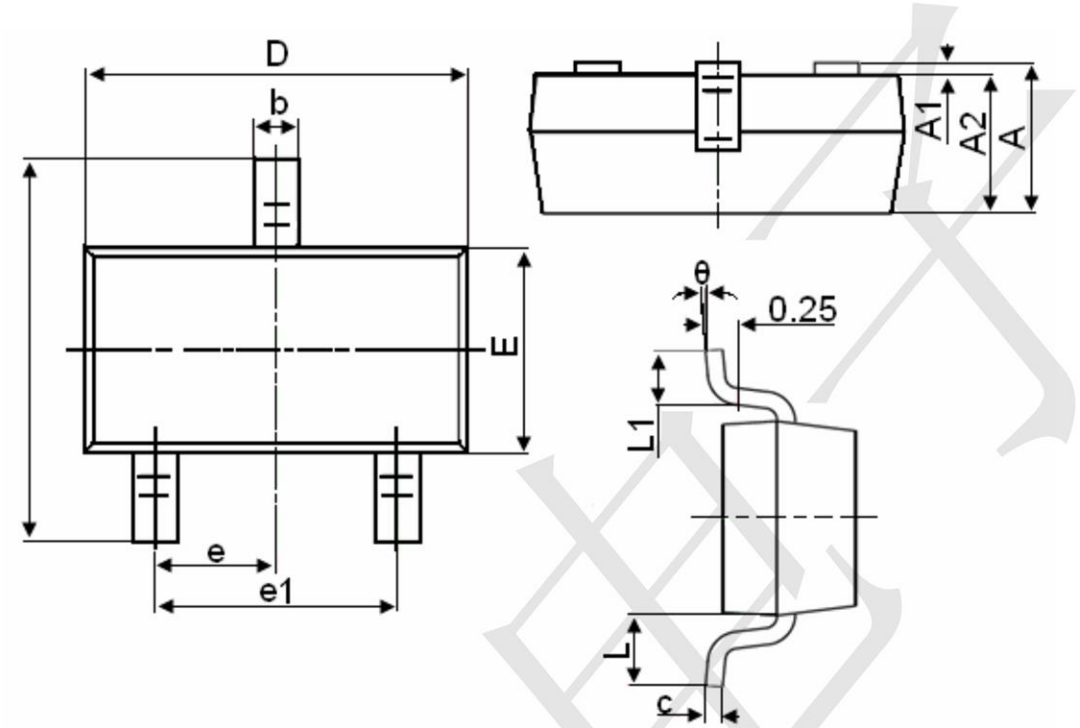


Fig6 Typical Capacitance Vs.Drain-Source Voltage

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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